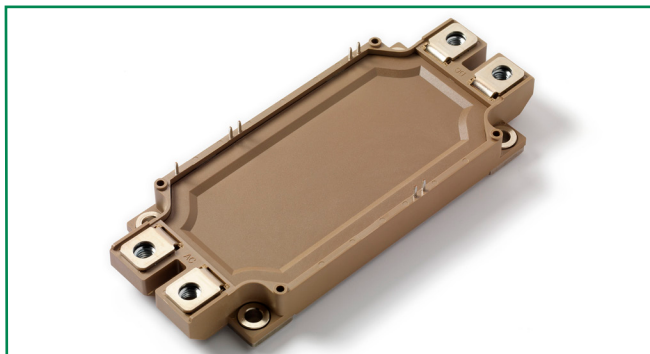


MG06600WB-BN4MM

RoHS



Features

- High short circuit capability, self limiting short circuit current
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast switching and short tail current
- Free wheeling diodes with fast and soft reverse recovery
- Low switching losses

Applications

- High frequency switching application
- Medical applications
- Motion/servo control supplies
- UPS systems

Module Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$T_{J\max}$	Max. Junction Temperature				175	$^\circ\text{C}$
T_{Jop}	Operating Temperature		-40		150	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40		125	$^\circ\text{C}$
V_{isol}	Insulation Test Voltage	AC, t=1min		3000		V
CTI	Comparative Tracking Index		250			
Torque	Module-to-Sink	Recommended (M5)	2.5		5	N·m
Torque	Module Electrodes	Recommended (M6)	3		5	N·m
Weight				350		g

Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage	$T_J = 25^\circ\text{C}$	600	V
V_{GES}	Gate - Emitter Voltage		± 20	V
I_C	DC Collector Current	$T_C = 25^\circ\text{C}$	700	A
		$T_C = 50^\circ\text{C}$	600	A
I_{CM}	Repetitive Peak Collector Current	$t_p = 1\text{ms}$	1200	A
P_{tot}	Power Dissipation Per IGBT		1500	W
Diode				
V_{RRM}	Repetitive Reverse Voltage	$T_J = 25^\circ\text{C}$	600	V
$I_{F(AV)}$	Average Forward Current	$T_C = 25^\circ\text{C}$	700	A
		$T_C = 50^\circ\text{C}$	600	A
I_{FRM}	Repetitive Peak Forward Current	$t_p = 1\text{ms}$	1200	A
I^2t		$T_J = 125^\circ\text{C}$, $t = 10\text{ms}$, $V_R = 0\text{V}$	17000	A^2s

Power Module

600V 600A IGBT Module

Electrical and Thermal Specifications ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions		Min	Typ	Max	Unit
IGBT							
V _{GE(th)}	Gate - Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =9.6mA		4.9	5.8	6.5	V
V _{CE(sat)}	Collector - Emitter	I _C =600A, V _{GE} =15V, T _J =25°C			1.45		V
	Saturation Voltage	I _C =600A, V _{GE} =15V, T _J =125°C			1.6		V
I _{ICES}	Collector Leakage Current	V _{CE} =600V, V _{GE} =0V, T _J =25°C				1	mA
		V _{CE} =600V, V _{GE} =0V, T _J =125°C				5	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V, V _{GE} =±15V, T _J =125°C		-400		400	nA
R _{Gint}	Integrated Gate Resistor				0.68		Ω
Q _{ge}	Gate Charge	V _{CE} =300V, I _C =600A , V _{GE} =±15V			6.5		μC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =1MHz			39		nF
C _{res}	Reverse Transfer Capacitance				1.15		nF
t _{d(on)}	Turn - on Delay Time	V _{CC} =300V I _C =600A R _G =2.4Ω V _{GE} =±15V Inductive Load	T _J =25°C		100		ns
			T _J =125°C		110		ns
t _r	Rise Time		T _J =25°C		90		ns
			T _J =125°C		95		ns
t _{d(off)}	Turn - off Delay Time		T _J =25°C		670		ns
			T _J =125°C		710		ns
t _f	Fall Time		T _J =25°C		70		ns
			T _J =125°C		75		ns
E _{on}	Turn - on Energy		T _J =25°C		8.9		mJ
			T _J =125°C		9.9		mJ
E _{off}	Turn - off Energy		T _J =25°C		21.5		mJ
			T _J =125°C		25		mJ
I _{SC}	Short Circuit Current	t _{pse} ≤6μS , V _{GE} =15V; T _J =125°C , V _{CC} =360V			3000		A
R _{thJC}	Junction-to-Case Thermal Resistance (Per IGBT)					0.10	K/W
Diode							
V _F	Forward Voltage	I _F =600A, V _{GE} =0V, T _J =25°C			1.55		V
		I _F =600A, V _{GE} =0V, T _J =125°C			1.5		V
t _{RR}	Reverse Recovery Time	I _F =600A, V _R =300V di _F /dt=-6000A/μs T _J =125°C			400		ns
I _{RRM}	Max. Reverse Recovery Current				300		A
E _{rec}	Reverse Recovery Energy				9.3		mJ
R _{thJCD}	Junction-to-Case Thermal Resistance (Per Diode)					0.16	K/W

NTC Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
R_{25}	Resistance	$T_c=25^\circ\text{C}$		5		K Ω
$B_{25/50}$				3375		K

Figure 1: Typical Output Characteristics for IGBT Inverter

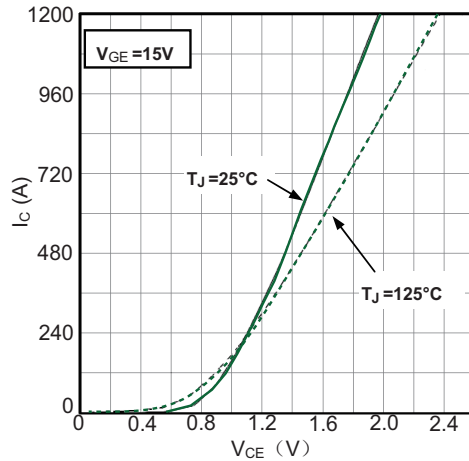


Figure 2: Typical Output Characteristics for IGBT Inverter

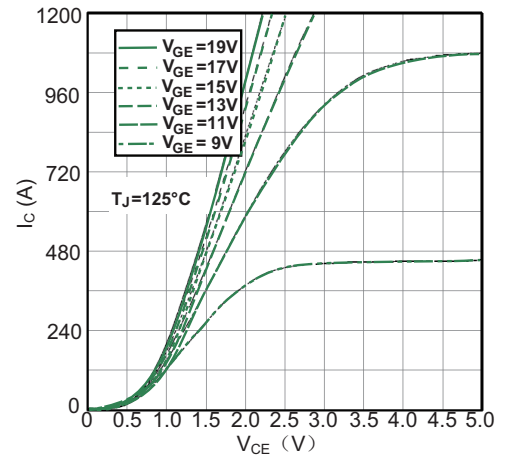


Figure 3: Typical Transfer Characteristics for IGBT Inverter

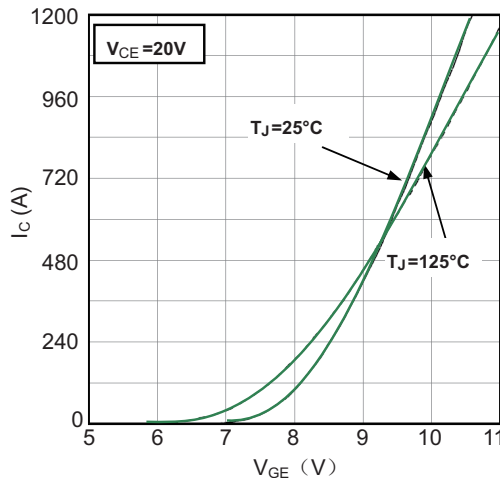


Figure 4: Switching Energy vs. Gate Resistor for IGBT Inverter

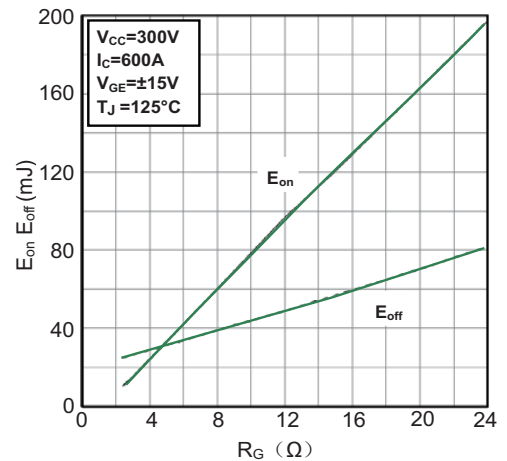


Figure 5: Switching Energy vs. Collector Current for IGBT Inverter

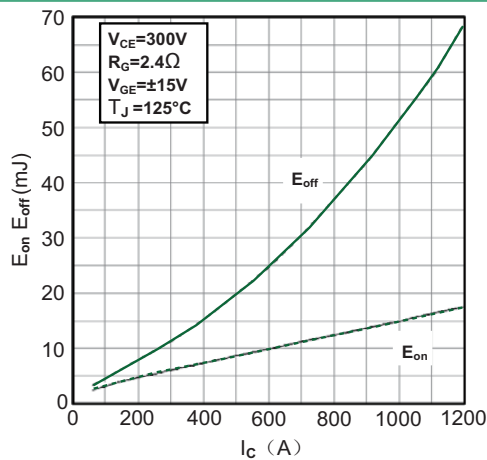


Figure 6: Reverse Biased Safe Operating Area for IGBT Inverter

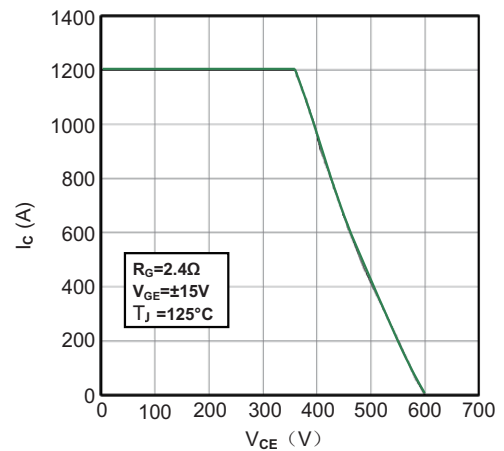


Figure 7: Diode Forward Characteristics for Diode Inverter

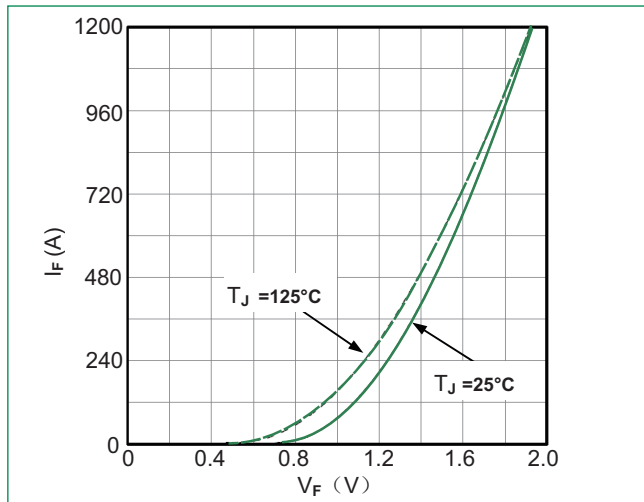


Figure 8: Switching Energy vs. Gate Resistort for Diode Inverter

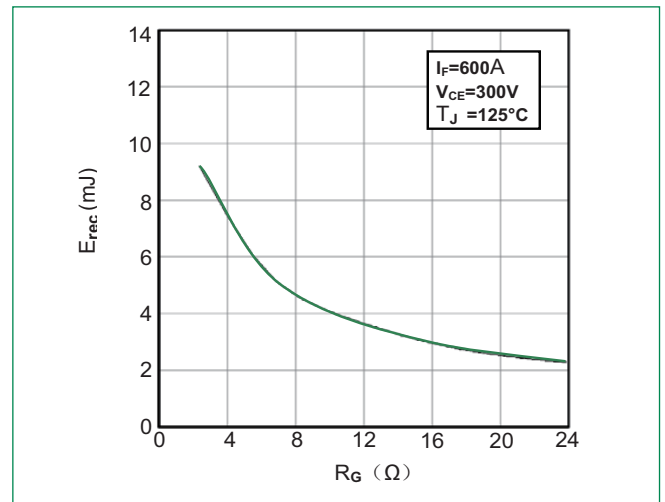


Figure 9: Transient Thermal Impedance of Diode and IGBT Inverter

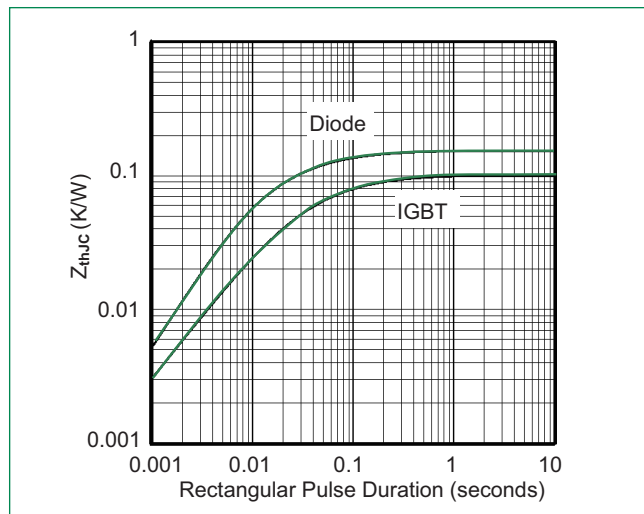
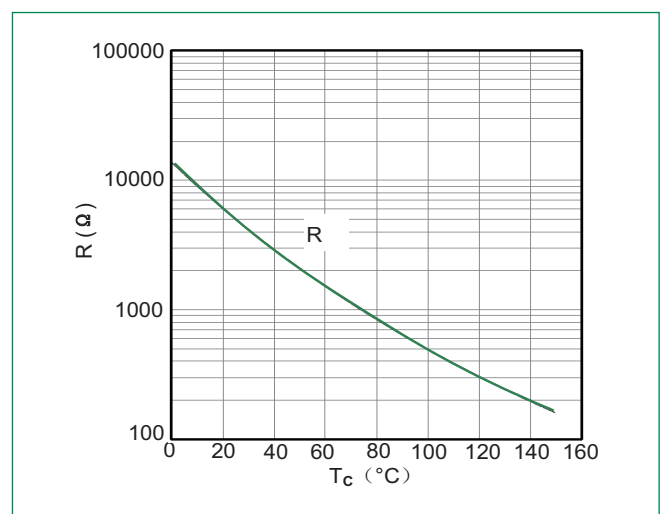
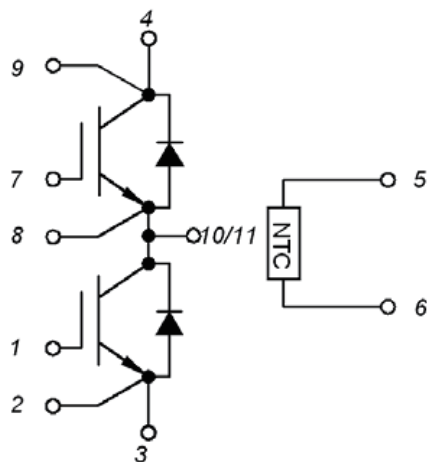


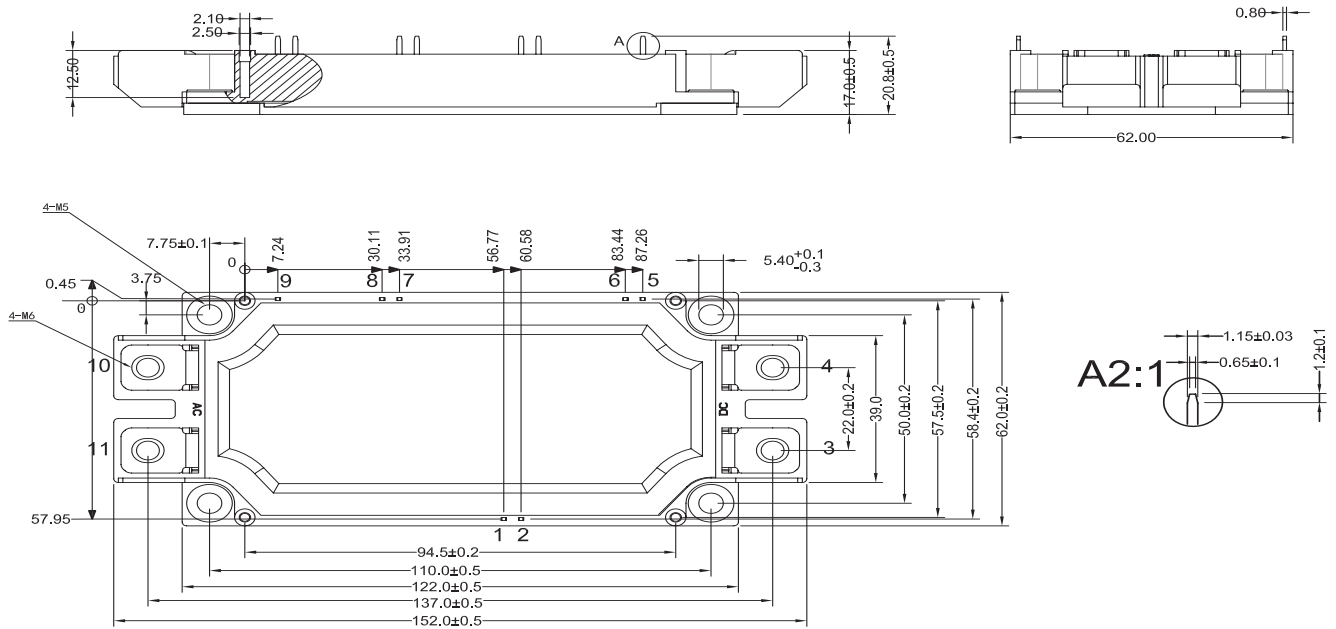
Figure 10: NTC Characteristics



Circuit Diagram



Dimensions-Package WB

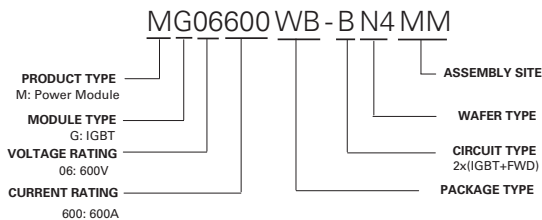


The foot pins are in gold / nickel coating

Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG06600WB-BN4MM	MG06600WB-BN4MM	350g	Bulk Pack	60

Part Numbering System



Part Marking System

